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Yuzo Shinozuka received his doctoral thesis from the University of Tokyo, Japan, in 1980. Then he engaged in the theoretical research of semiconductor physics first at Yamaguchi University and then at Wakayama University. His interest is in making simple models to explain mysterious phenomena. The main subjects are various electronic and atomic processes induced by electron–lattice interactions in non-metallic materials, including intrinsic and extrinsic self-trapping, nonradiative recombination, deep levels, defect reaction, and material modification by electronic excitations. Dr. Shinozuka also participated in the theory of electronic states in alloy semiconductors. He is now a professor emeritus at Wakayama University.

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